

Prof. ŞEMSETTİN ALTINDAL

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Education Information

Doctorate, Gazi University, Fen Bilimleri Enstitüsü, Fizik (Dr), Turkey 1986 - 1994

Post Graduate, Gazi University, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), Turkey 1983 - 1985

Under Graduate, Firat University, Fen Fakültesi, Fizik Bölümü, Turkey 1978 - 1982

Dissertations

Doctorate, Al-siox-psi aygıtların ve güneş pillerinin elektriksel karakteristikleri, Gazi University, Fen Bilimleri Enstitüsü, Fizik (Dr), 1993

Post Graduate, Çok ince yapı teorisi, Gazi University, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), 1950

Academic Titles / Tasks

Professor, Gazi University, Fen Fakültesi, Fizik Bölümü, 2011 - Continues

Associate Professor, Gazi University, Fen Fakültesi, Fizik Bölümü, 2005 - 2011

Assistant Professor, Gazi University, Fen Fakültesi, Fizik Bölümü, 1994 - 2005

Research Assistant, Gazi University, Fen Fakültesi, Fizik Bölümü, 1983 - 1994

Advising Theses

ALTINDAL Ş., Au/(Ag-ZnO/PVP)/n-Si (MPS) SCHOTTKY ENGEL DİYOTLARIN HAZIRLANMASI VE ELEKTRİK İLE DİELEKTRİK ÖZELLİKLERİNİN FREKANS VE VOLTAJA BAĞLI İNCELENMESİ, Doctorate, Ö.SEVGİLİ(Student), 2020

ALTINDAL Ş., USLU İ., Production And Characterization Of Graphene Doped P-Type And N-Type Thermoelectric Nanocomposite Material, Post Graduate, S.KOÇYİĞİT(Student), 2017

ALTINDAL Ş., The Comparison Of Electrical Characteristics Of Schottky Barrier Diodes With And Without Polymer Interfacial Layer, Doctorate, Ç.BİLKAN(Student), 2016

ALTINDAL Ş., USLU İ., Zirkonyum oksit ve gadolinyum oksit tabanlı çeşitli metal oksit katkılı inorganik pigmentlerin çöz-pel tekniğiyle sentezi ve karakterizasyonu, Post Graduate, A.AYTİMUR(Student), 2015

ALTINDAL Ş., The Investigation Of Frequency And Voltage Dependence Of Main Electrical Parametres Of Au/Zno/N-Gaas (Mıs) Schottky Barrier Diodes (Sbds), Post Graduate, B.AKIN(Student), 2015

ALTINDAL Ş., Electrical And Dielectric Properties Of Au/(%1 Graphene (Gp) Doped)-Ca_{1.9}pr_{0.1}co₄ox /N-Si Schottky Barrier Diodes As Function Of Temperature And Frequency, H.Gökçen(Student), 2015

ALTINDAL Ş., USLU İ., The Fabrication And Characterization Of Polyvinylidene Fluoride Nanocomposite Piezomaterials Doped Graphene, Boron And Rare Earth Elements, Post Graduate, Y.BADALI(Student), 2015

ALTINDAL Ş., The Fabrication Of Au/N-Gaas Schottky Diodes And The Investigation Of Their Current-Conduction Mechanisms In Wide Temperature Range, Doctorate, E.ÖZAVCI(Student), 2015

ALTINDAL Ş., Forward And Reverse Bias Current-Voltage (I-V) Characteristics Of Au/Ca₃Co₄Ga_{0,001}Ox/n-Si Structures In Temperature Range Of 80-340 K, Doctorate, E.MARIL(Student), 2015

ALTINDAL Ş., Au/(%1 grafen (GP) katkılı)-Ca_{1.9}Pr_{0.1}Co₄O_x/n-Si Schottky engel diyotların hazırlanması ve elektrik ile dielektrik özelliklerinin sıcaklık ve frekansa bağlı incelenmesi, Doctorate, H.GÖKÇEN(Student), 2015

ALTINDAL Ş., The Preperation Of Au/Pva:Zn/N-Si (Mps) Structures And Investigation Of Main Electrical Characteristics Under Illumination, Doctorate, U.AYDEMİR(Student), 2014

ALTINDAL Ş., The preparation of Au/(Zn-Doped) polyvinyl alcohol/n-GaAs structures and the investigation of their current-transport mechanisms in the wide temperature, Doctorate, H.TECİMER(Student), 2014

ALTINDAL Ş., The investigation of electrical and dielectric properties of metal-polymer-semiconductor (MPS) structures in the wide frequency range, Doctorate, A.KAYA(Student), 2013

ALTINDAL Ş., The preparation of Au/n-4H-SiC (MS) schottky diodes and the investigation their electrical characteristics as function of frequency, Post Graduate, Ö.SEVGİLİ(Student), 2013

ALTINDAL Ş., A comparative study on the electrical characterization of Al/p-Si (MS) structures with and without interfacial perylene (C₂₀H₁₂) layer at room temperature, Post Graduate, Ç.BİLKAN(Student), 2013

ALTINDAL Ş., Metal-yalıtkan-yarıiletken (Al/SiO₂/p-Si) yapıların elektrik ve dielektrik özelliklerinin frekans ve potansiyele bağlı incelenmesi, Doctorate, Z.SÖNMEZ(Student), 2012

ALTINDAL Ş., The investigation of electrical properties of (Ni/Au)/Al_{0.22}Ga_{0.78}N/AlN/GaN hetero-structures by using admittance spectroscopy method, Doctorate, Y.ŞAFAK(Student), 2012

ALTINDAL Ş., The investigation of temperature and radiation dependent electrical characteristics of au/pva:zn/n-si (mps) schottky barrier diodes, Doctorate, İ.TAŞÇIOĞLU(Student), 2012

ALTINDAL Ş., Au/(Bi-katkılı) polivinil alkol/n-si schottky engel diyotlarının elektriksel özelliklerinin sıcaklığa ve aydınlatma şiddetine bağlı incelenmesi, Post Graduate, H.GÖKÇEN(Student), 2011

ALTINDAL Ş., The investigation of temperature dependent electric and dielectric characteristics of Au/SiO₂/n-Si (MIS) structure, Post Graduate, A.GÜL(Student), 2011

ALTINDAL Ş., The preparation of al/rhodamine-101/n-gaas schottky barrier diodes and the investigation of their conduction mechanisms in the wide temperature range, Doctorate, Ö.VURAL(Student), 2011

ALTINDAL Ş., SiO₂/p-Si (MIS) YAPILARIN ELEKTRİK KARAKTERİSTİKLERİNİN FREKANS BAĞLI İNCELENMESİ, A.KAYA(Student), 2010

ALTINDAL Ş., NiAu-AlGa_n/Ga_n heteroyapıların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Doctorate, S.DEMİREZEN(Student), 2010

ALTINDAL Ş., NiAu-AlGa_n/Ga_n HETEROYAPILARIN ELEKTRİKSEL KARAKTERİSTİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, S.DEMİREZEN(Student), 2010

ALTINDAL Ş., The preparation of Au/polyvinyl alcohol (Co, Zn-doped)/n-Si schottky barrier diodes and the investigation of their electrical characteristics as a function of illumination intensity, Doctorate, H.USLU(Student), 2010

ALTINDAL Ş., Al/SiO₂/p-Si (MIS) yapıların elektrik karakteristiklerinin frekansa bağlı incelenmesi, Post Graduate, A.KAYA(Student), 2010

ALTINDAL Ş., THE INVESTIGATION OF FREQUENCY DEPENDENT ELECTRICAL CHARACTERIZATION OF Au/SrTiO₃/n-Si (MFS) SCHOTTKY DIODES, Post Graduate, U.AYDEMİR(Student), 2009

ALTINDAL Ş., THE INVESTIGATION OF TEMPERATURE DEPENDENCE CURRENT-CONDUCTION MECHANISM AND ELECTRICAL CHARACTERISTICS OF Al/SiO₂/p-Si (MIS) STRUCTURES, D.Esra(Student), 2008

ALTINDAL Ş., Au/SiO₂/n-GaAs (MOY) yapıların elektrik ve dielektrik karakteristiklerinin frekans ve sıcaklığa bağlı incelenmesi, Doctorate, M.GÖKÇEN(Student), 2008

ALTINDAL Ş., Al/SiO₂/p-Si (MY) yapıların akım iletim mekanizması ve elektriksel özelliklerinin sıcaklığa bağlı incelenmesi, Doctorate, D.ESRA(Student), 2008

ALTINDAL Ş., THE INVESTIGATION OF TEMPERATURE DEPENDENCE OF ELECTRICAL CHARACTERISTICS OF THE Al/p-Si SCHOTTKY DIODES WITH INSULATOR LAYER, Doctorate, H.KANBUR(Student), 2008

ALTINDAL Ş., THE INVESTIGATION OF FREQUENCY AND TEMPERATURE DEPENDENCE OF ELECTRICAL AND DIELECTRIC PROPERTIES OF Au/SiO₂/n-GaAs (MOS) STRUCTURES, M.GÖKÇEN(Student), 2008

ALTINDAL Ş., Metal-yalıtkan-yarı iletken (MIS) yapılarda elektrik ve dielektrik özelliklerinin sıcaklık ve frekansa bağlı incelenmesi, Doctorate, İ.YÜCEDAĞ(Student), 2007

ALTINDAL Ş., Schottky diyotların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Post Graduate, H.KUTLUCA(Student), 2007

ALTINDAL Ş., INVESTIGATION OF ELECTRICAL CHARACTERISTICS OF (Al-TiW+PtSi)-n-Si SCHOTTKY DIODES

DEPENDING ON FREQUENCY AND ILLUMINATION, Post Graduate, M.HAMDİ(Student), 2007

ALTINDAL Ş., THE PREPARATION OF Au/Bi₄Ti₃O₁₂/SiO₂/n-Si STRUCTURES, INVESTIGATION OF THE ELECTRICAL AND DIELECTRIC PROPERTIES BASED ON FREQUENCY AND TEMPERATURE, F.PARLAKTÜRK(Student), 2007

ALTINDAL Ş., THE INVESTIGATION OF TEMPERATURE DEPENDENT ELECTRICAL CHARACTERISTICS OF SCHOTTKY DIODES, H.KUTLUCA(Student), 2007

ALTINDAL Ş., Au/Bi₄Ti₃O₁₂/SiO₂/n-Si yapıların hazırlanması, elektriksel ve dielektrik özelliklerinin frekans ve sıcaklığa bağlı incelenmesi, Doctorate, F.PARLAKTÜRK(Student), 2007

ALTINDAL Ş., MIS yapıların frekans ve radyasyona bağlı temel elektriksel parametreleri, Post Graduate, B.TATAROĞLU(Student), 2006

ALTINDAL Ş., Doğal yalıtkan tabakalı Al/p-Si schottky diyotlarda elektriksel karakteristiklerin frekansa bağlı incelenmesi, Post Graduate, H.KAMBUR(Student), 2005

ALTINDAL Ş., (Al-TiW+PtSi)/n-Si Schottky diyotlarının sıcaklığa bağlı temel parametreleri, Post Graduate, E.MARIL(Student), 2005

ALTINDAL Ş., Doğal yalıtkan tabakalı Al/p-Si Schottky diyotlarda elektriksel karakteristiklerin frekansa bağlı incelenmesi, Post Graduate, H.KANBUR(Student), 2005

ALTINDAL Ş., MOS yapılarda temel fiziksel parametrelerin frekans ve radyasyon miktarına bağlı incelenmesi, Doctorate, A.TATAROĞLU(Student), 2004

ALTINDAL Ş., MOS yapılarda kapasitans-voltaj (C-V) ve iletkenlik voltaj (G/W-V) karakteristiklerinin frekans ve radyasyona bağlı incelenmesi, Post Graduate, M.GÖKÇEN(Student), 2003

ALTINDAL Ş., Yalıtkan arayüzey tabakası ve seri dirence sahip Al/ SnO₂/ p-Si schottky diyotların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Post Graduate, Z.TEKELİ(Student), 2002

ALTINDAL Ş., Al/p-Si ve Au/n-Si schottky diyotlarda I-V ve C-V karakteristiklerinin geniş bir sıcaklık aralığında analizi, Doctorate, İ.DÖKME(Student), 2002

ALTINDAL Ş., Güneş pillerinde arayüzey durumlarının c.v. karakteristiklerine etkisi, Post Graduate, E.YILDIZ(Student), 1999

ALTINDAL Ş., Metal-oksit-yarıiletken (MOS) kapasitörlerde dielektrik sabitinin frekans, sıcaklık ve kalınlığa bağlı incelenmesi, Post Graduate, A.TATAROĞLU(Student), 1999

ALTINDAL Ş., Arayüz oksit tabakası ve seri dirence sahip rult-n-Si schottky diyod parametrelerinin doğru beslem I-V ve C-V karakteristiklerinden hesaplanması, Post Graduate, Ö.VURAL(Student), 1998

ALTINDAL Ş., Al-SiO₂-pSi (MY) güneş pillerinin sıcaklığa bağlı elektriksel karakteristikleri, Post Graduate, C.TEMEL(Student), 1997

Articles Published in Journals That Entered SCI, SSCI and AHCI Indexes

- I. **The effect of cadmium impurities in the (PVP-TeO₂) interlayer in Al/p-Si (MS) Schottky barrier diodes (SBDs): Exploring its electrophysical parameters**
Pirgholi-Givi G., ALTINDAL Ş., Shahedi Asl M., Sabahi Namini A., Farazin J., Azizian-Kalandaragh Y.
Physica B: Condensed Matter, vol.604, 2021 (Journal Indexed in SCI Expanded)
- II. **Investigation of the variation of dielectric properties by applying frequency and voltage to Al/(CdS-PVA)/p-Si structures**
Azizian-Kalandaragh Y., Yucedag I., Demir G. E. , ALTINDAL Ş.
Journal of Molecular Structure, vol.1224, 2021 (Journal Indexed in SCI Expanded)
- III. **Current transport properties of (Au/Ni)/HfAlO₃/n-Si metal-insulator-semiconductor junction**
Arslan E., Badali Y., Aalizadeh M., ALTINDAL Ş., Ozbay E.
JOURNAL OF PHYSICS AND CHEMISTRY OF SOLIDS, vol.148, 2021 (Journal Indexed in SCI)
- IV. **Electrical characterization of Au/n-Si (MS) diode with and without graphene-polyvinylpyrrolidone (Gr-PVP) interface layer**
TATAROĞLU A., ALTINDAL Ş., Azizian-Kalandaragh Y.
Journal of Materials Science: Materials in Electronics, 2021 (Journal Indexed in SCI Expanded)
- V. **On the Multi-parallel Diodes Model in Au/PVA/n-GaAs Schottky Diodes and Investigation of**

Conduction Mechanisms (CMs) in a Temperature Range of 80-360 K

Evcin Baydilli E., Kaymaz A., Uslu Tecimer H., Altindal Ş.

JOURNAL OF ELECTRONIC MATERIALS, vol.49, is.12, pp.7427-7434, 2020 (Journal Indexed in SCI)

- VI. **A Highly Sensitive Temperature Sensor Based on Au/Graphene-PVP/n-Si Type Schottky Diodes and the Possible Conduction Mechanisms in the Wide Range Temperatures**
ÇİÇEK O., ALTINDAL Ş., Azizian-Kalandaragh Y.
IEEE Sensors Journal, vol.20, is.23, pp.14081-14089, 2020 (Journal Indexed in SCI Expanded)
- VII. **Effect of illumination on electrical parameters of Au/(P3DMTFT)/n-GaAs Schottky barrier diodes**
Lapa H. E., KÖKCE A., ALDEMİR D. A., ÖZDEMİR A. F., ALTINDAL Ş.
INDIAN JOURNAL OF PHYSICS, vol.94, is.12, pp.1901-1908, 2020 (Journal Indexed in SCI)
- VIII. **Detection of current transport mechanisms for graphene-doped-PVA interlayered metal/semiconductor structures**
Baydilli E. E., Tan S. O., Tecimer H. U., Altindal Ş.
PHYSICA B-CONDENSED MATTER, vol.598, 2020 (Journal Indexed in SCI)
- IX. **On the electrical characteristics of Al/p-Si diodes with and without (PVP: Sn-TeO₂) interlayer using current-voltage (I-V) measurements**
Sabahi Namini A., Shahedi Asl M., Pirgholi-Givi G., Delbari S. A., Farazin J., ALTINDAL Ş., Azizian-Kalandaragh Y.
Applied Physics A: Materials Science and Processing, vol.126, is.12, 2020 (Journal Indexed in SCI Expanded)
- X. **The interfacial properties of Au/n-4H-SiC structure with (Zn-doped PVA) interfacial layer**
Lapa H. E., KÖKCE A., ALDEMİR D. A., ÖZDEMİR A. F., ALTINDAL Ş.
PHYSICA SCRIPTA, vol.95, is.11, 2020 (Journal Indexed in SCI)
- XI. **The possible current-conduction mechanism in the Au/(CoSO₄-PVP)/n-Si junctions**
Elamen H., Badali Y., GÜNEŞER M. T., ALTINDAL Ş.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.31, is.21, pp.18640-18648, 2020 (Journal Indexed in SCI)
- XII. **Investigation of effects on dielectric properties of different doping concentrations of Au/Gr-PVA/p-Si structures at 0.1 and 1 MHz at room temperature**
Ersoz Demir G., Yucedag I., ALTINDAL Ş.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.31, is.19, pp.16324-16331, 2020 (Journal Indexed in SCI)
- XIII. **The determination of the temperature and voltage dependence of the main device parameters of Au/7%Gr-doped PVA/n-GaAs-type Schottky Diode (SD)**
Evcin Baydilli E., Altindal Ş., Tecimer H., Kaymaz A., Uslu Tecimer H.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.31, is.20, pp.17147-17157, 2020 (Journal Indexed in SCI)
- XIV. **On the frequency and voltage-dependent main electrical parameters of the Au/ZnO/n-GaAs structures at room temperature by using various methods**
Akin B., ALTINDAL Ş.
PHYSICA B-CONDENSED MATTER, vol.594, 2020 (Journal Indexed in SCI)
- XV. **A comparative study on the electrical properties and conduction mechanisms of Au/n-Si Schottky diodes with/without an organic interlayer**
Eroglu A., DEMİREZEN S., Azizian-Kalandaragh Y., ALTINDAL Ş.
Journal of Materials Science: Materials in Electronics, vol.31, is.17, pp.14466-14477, 2020 (Journal Indexed in SCI Expanded)
- XVI. **Electric and dielectric parameters in Au/n-Si (MS) capacitors with metal oxide-polymer interlayer as function of frequency and voltage**
DEMİREZEN S., Eroglu A., Azizian-Kalandaragh Y., ALTINDAL Ş.
Journal of Materials Science: Materials in Electronics, vol.31, is.18, pp.15589-15598, 2020 (Journal Indexed in SCI Expanded)
- XVII. **The origin of anomalous peak and negative capacitance on dielectric behavior in the accumulation region in Au/(0.07 Zn-doped polyvinyl alcohol)/n-4H-SiC metal-polymer-semiconductor**

structures/diodes studied by temperature-dependent impedance measurements

Al-Dharob M. H. , KÖKCE A., ALDEMİR D. A. , ÖZDEMİR A. F. , ALTINDAL Ş.

JOURNAL OF PHYSICS AND CHEMISTRY OF SOLIDS, vol.144, 2020 (Journal Indexed in SCI)

- XVIII. **Electrical characteristics of Au/PVP/n-Si structures using admittance measurements between 1 and 500 kHz**
ALPTEKİN S., ALTINDAL Ş.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.31, is.16, pp.13337-13343, 2020 (Journal Indexed in SCI)
- XIX. **Electrical and dielectric properties of Al/(PVP: Zn-TeO₂)/p-Si heterojunction structures using current-voltage (I-V) and impedance-frequency (Z-f) measurements**
Azizian-Kalandaragh Y., Farazin J., ALTINDAL Ş., Asl M. S. , Pirgholi-Givi G., Delbari S. A. , Namini A. S.
Applied Physics A: Materials Science and Processing, vol.126, is.8, 2020 (Journal Indexed in SCI Expanded)
- XX. **A comparison study regarding Al/p-Si and Al/(carbon nanofiber-PVP)/p-Si diodes: current/impedance-voltage (I/Z-V) characteristics**
SEVGİLİ Ö., YILDIRIM M., Azizian-Kalandaragh Y., ALTINDAL Ş.
Applied Physics A: Materials Science and Processing, vol.126, is.8, 2020 (Journal Indexed in SCI Expanded)
- XXI. **Intersection behavior of the current-voltage (I-V) characteristics of the (Au/Ni)/HfAlO₃/n-Si (MIS) structure depends on the lighting intensity**
Arslan E., Badali Y., ALTINDAL Ş., ÖZBAY E.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.31, is.16, pp.13167-13172, 2020 (Journal Indexed in SCI)
- XXII. **Electrical and photoresponse properties of CoSO₄-PVP interlayer based MPS diodes**
Tataroglu A., Altindal Ş., Azizian-Kalandaragh Y.
Journal of Materials Science: Materials in Electronics, vol.31, is.14, pp.11665-11672, 2020 (Journal Indexed in SCI Expanded)
- XXIII. **Frequency-Dependent Admittance Analysis of Au/n-Si Structure with CoSO₄-PVP Interfacial Layer**
Tascioglu I., SEVGİLİ Ö., Azizian-Kalandaragh Y., ALTINDAL Ş.
Journal of Electronic Materials, vol.49, is.6, pp.3720-3727, 2020 (Journal Indexed in SCI Expanded)
- XXIV. **Investigation of gamma-irradiation effects on electrical characteristics of Al/(ZnO-PVA)/p-Si Schottky diodes using capacitance and conductance measurements**
KAYMAZ A., Tecimer H. U. , Baydilli E. E. , ALTINDAL Ş.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.31, is.11, pp.8349-8358, 2020 (Journal Indexed in SCI)
- XXV. **Investigation of the effect of different Bi₂O₃-x:PVA (x = Sm, Sn, Mo) thin insulator interface-layer materials on diode parameters**
Badali Y., Azizian-Kalandaragh Y., USLU İ., ALTINDAL Ş.
Journal of Materials Science: Materials in Electronics, vol.31, is.10, pp.8033-8042, 2020 (Journal Indexed in SCI Expanded)
- XXVI. **C-V-f and G/ω-V-f characteristics of Au/(In₂O₃-PVP)/n-Si (MPS) structure**
Tataroglu A., Altindal Ş., Azizian-Kalandaragh Y.
Physica B: Condensed Matter, vol.582, 2020 (Journal Indexed in SCI Expanded)
- XXVII. **Frequency and voltage dependence of barrier height, surface states, and series resistance in Al/Al₂O₃/p-Si structures in wide range frequency and voltage**
Turk C. G. , TAN S. O. , ALTINDAL Ş., İNEM B.
PHYSICA B-CONDENSED MATTER, vol.582, 2020 (Journal Indexed in SCI)
- XXVIII. **The effects of (Bi₂Te₃-Bi₂O₃-TeO₂-PVP) interfacial film on the dielectric and electrical features of Al/p-Si (MS) Schottky barrier diodes (SBDs)**
ALTINDAL Ş., Farazin J., Pirgholi-Givi G., MARIL E., Azizian-Kalandaragh Y.
Physica B: Condensed Matter, vol.582, 2020 (Journal Indexed in SCI Expanded)
- XXIX. **Investigation of Dielectric Properties, Electric Modulus and Conductivity of the Au/Zn-Doped PVA/n-4H-SiC (MPS) Structure Using Impedance Spectroscopy Method**

Lapa H. E., KÖKCE A., ÖZDEMİR A. F., ALTINDAL Ş.

ZEITSCHRIFT FÜR PHYSIKALISCHE CHEMIE-INTERNATIONAL JOURNAL OF RESEARCH IN PHYSICAL CHEMISTRY & CHEMICAL PHYSICS, vol.234, is.3, pp.505-516, 2020 (Journal Indexed in SCI)

- XXX. **A Compare Study on Electrical Properties of MS Diodes with and Without CoFe₂O₄-PVP Interlayer**
Tataroglu A., Buyukbas Ulan A., Altindal Ş., Azizian-Kalendaragh Y.
Journal of Inorganic and Organometallic Polymers and Materials, 2020 (Journal Indexed in SCI Expanded)
- XXXI. **Frequency Response of C-V and G/ω-V Characteristics of Au/(Nanographite-doped PVP)/n-Si Structures**
Akbas A. M., ÇİÇEK O., ALTINDAL Ş., Azizian-Kalendaragh Y.
Journal of Materials Science: Materials in Electronics, 2020 (Journal Indexed in SCI Expanded)
- XXXII. **Ultrasound-Assisted Method for Preparation of Ag₂S Nanostructures: Fabrication of Au/Ag₂S-PVA/n-Si Schottky Barrier Diode and Exploring Their Electrical Properties**
Badali Y., Azizian-Kalendaragh Y., Akhlaghi E. A., Altindal Ş.
Journal of Electronic Materials, vol.49, is.1, pp.444-453, 2020 (Journal Indexed in SCI Expanded)
- XXXIII. **Comparison of electrical properties of MS and MPS type diode in respect of (In₂O₃-PVP) interlayer**
TATAROĞLU A., ALTINDAL Ş., Azizian-Kalendaragh Y.
Physica B: Condensed Matter, vol.576, 2020 (Journal Indexed in SCI Expanded)
- XXXIV. **Identifying of series resistance and interface states on rhenium/n-GaAs structures using C-V-T and G/-V-T characteristics in frequency ranged 50 kHz to 5 MHz**
ÇİÇEK O., DURMUŞ H., ALTINDAL Ş.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.31, is.1, pp.704-713, 2020 (Journal Indexed in SCI)
- XXXV. **Determination of current transport and trap states density in AlInGaN/GaN heterostructures**
Arslan E., Ural S., ALTINDAL Ş., ÖZBAY E.
MICROELECTRONICS RELIABILITY, vol.103, 2019 (Journal Indexed in SCI)
- XXXVI. **Investigation of the efficiencies of the (SnO₂-PVA) interlayer in Au/n-Si (MS) SDs on electrical characteristics at room temperature by comparison**
BİLKAN Ç., Azizian-Kalendaragh Y., SEVGİLİ Ö., ALTINDAL Ş.
Journal of Materials Science: Materials in Electronics, vol.30, is.23, pp.20479-20488, 2019 (Journal Indexed in SCI Expanded)
- XXXVII. **Dielectric properties of Ag/Ru-0.03-PVA/n-Si structures**
Badali Y., Kocyigit S., USLU İ., ALTINDAL Ş.
BULLETIN OF MATERIALS SCIENCE, vol.42, is.5, 2019 (Journal Indexed in SCI)
- XXXVIII. **Synthesis of boron and rare earth stabilized graphene doped polyvinylidene fluoride (PVDF) nanocomposite piezoelectric materials**
Badali Y., Kocyigit S., Aytimur A., ALTINDAL Ş., USLU İ.
POLYMER COMPOSITES, vol.40, is.9, pp.3623-3633, 2019 (Journal Indexed in SCI)
- XXXIX. **Dielectric characterization of BSA doped-PANI interlayered metal-semiconductor structures**
KARAOĞLAN N., Tecimer H. U., ALTINDAL Ş., BİNDAL C.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.30, is.15, pp.14224-14232, 2019 (Journal Indexed in SCI)
- XL. **Examination of dielectric response of Au/HgS-PVA/n-Si (MPS) structure by impedance spectroscopy method**
SEVGİLİ Ö., Tascioglu I., Boughdachi S., Azizian-Kalendaragh Y., ALTINDAL Ş.
Physica B: Condensed Matter, vol.566, pp.125-135, 2019 (Journal Indexed in SCI Expanded)
- XLI. **A comparative study on the electrical and dielectric properties of Al/Cd-doped ZnO/p-Si structures**
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